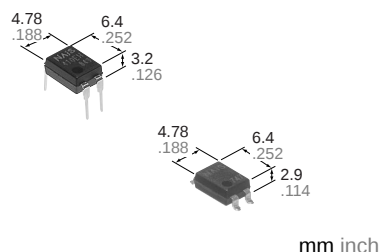


NAiS

GU (General Use)-E Type 1-Channel (Form B) 4-pin Type

PhotoMOS RELAYS

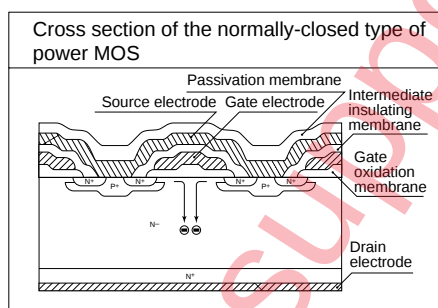


FEATURES

1. Low on resistance for normally-closed type

This has been realized thanks to the built-in MOSFET processed by our proprietary method, DSD (Double-diffused and Selective Doping) method.

Cross section of the normally-closed type of power MOS



2. Reinforced insulation 5,000 V type

More than 0.4 mm internal insulation distance between inputs and outputs. Conforms to EN41003, EN60950 (reinforced insulation).

3. Compact 4-pin DIP size

The device comes in a compact (W)6.4×(L)4.78×(H)3.2mm (W).252×(L).188×(H).126inch, 4-pin DIP size

4. Controls low-level analog signals

PhotoMOS relays feature extremely low closed-circuit offset voltage to enable control of low-level analog signals without distortion.

5. High sensitivity, low ON resistance

Can control a maximum 0.13 A load current with a 5 mA input current. Low ON resistance of 18Ω (AQY410EH). Stable operation because there are no metallic contact parts.

6. Low-level off state leakage current

TYPICAL APPLICATIONS

- Modem
- Telephone equipment
- Security equipment
- Sensors

TYPES

Type	I/O isolation voltage	Output rating*		Part No.				Packing quantity	
				Through hole terminal	Surface-mount terminal				
		Load voltage	Load current	Tube packing style	Tape and reel packing style		Tube	Tape and reel	
					Picked from the 1/2-pin side	Picked from the 3/4-pin side			
AC/DC type	Reinforced 5,000 V	350 V	130 mA	AQY410EH	AQY410EHA	AQY410EHAX	AQY410EHAZ	1 tube contains 100 pcs. 1 batch contains 1,000 pcs.	1,000 pcs.
		400 V	120 mA	AQY414EH	AQY414EHA	AQY414EHAX	AQY414EHAZ		

*Indicate the peak AC and DC values.

Note: For space reasons, the initial letters of the product number "AQY", the SMD terminal shape indicator "A" and the package type indicator "X" and "Z" are omitted from the seal.

RATING

1. Absolute maximum ratings (Ambient temperature: 25°C 77°F)

Item		Symbol	AQY410EH (A)	AQY414EH (A)	Remarks
Input	LED forward current	I _F	50 mA		
	LED reverse voltage	V _R	3 V		
	Peak forward current	I _{FP}	1 A		f = 100 Hz, Duty factor = 0.1%
	Power dissipation	P _{in}	75 mW		
Output	Load voltage (peak AC)	V _L	350 V	400 V	
	Continuous load current	I _L	0.13 A	0.12 A	
	Peak load current	I _{peak}	0.4 A	0.3 A	100 ms (1 shot), V _L = DC
	Power dissipation	P _{out}	500 mW		
Total power dissipation		P _T	550 mW		
I/O isolation voltage		V _{iso}	5,000 V AC		
Temperature limits	Operating	T _{opr}	-40°C to +85°C -40°F to +185°F		Non-condensing at low temperatures
	Storage	T _{stg}	-40°C to +100°C -40°F to +212°F		

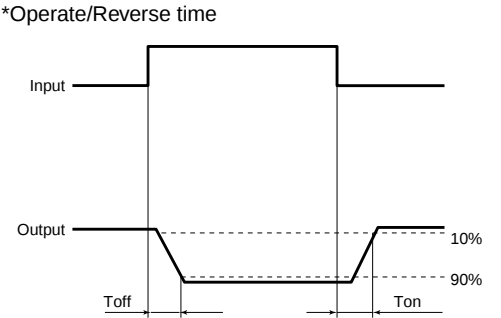
AQY410EH

2. Electrical characteristics (Ambient temperature: 25°C 77°F)

Item			Symbol	AQY410EH (A)	AQY414EH (A)	Condition
Input	LED operate (OFF) current	Typical	I _{Foff}	1.4 mA	1.3 mA	I _L =Max.
		Maximum		3.0 mA		
	LED reverse (ON) current	Minimum	I _{Fon}	0.4 mA		I _L =Max.
		Typical		1.3 mA	1.2 mA	
	LED dropout voltage	Typical	V _F	1.14 (1.25 V at I _F = 50 mA)		I _F = 5 mA
		Maximum		1.5 V		
Output	On resistance	Typical	R _{On}	18Ω	26Ω	I _F = 0 mA I _L = Max. Within 1 s on time
		Maximum		25Ω	35Ω	
	Off state leakage current	Maximum	I _{Leak}	10μA		I _F = 5 mA V _L = Max.
Transfer char- acteristics	Operate (OFF) time*	Typical	T _{off}	1.0 ms	0.8 ms	I _F = 0 mA-->5 mA I _L = Max.
		Maximum		3.0 ms		
	Reverse (ON) time*	Typical	T _{on}	0.3 ms	0.2 ms	I _F = 5 mA-->0 mA I _L = Max.
		Maximum		1.0 ms		
	I/O capacitance	Typical	C _{iso}	0.8 pF		f =1MHz V _B =0
		Maximum		1.5 pF		
	Initial I/O isolation resistance	Minimum	R _{iso}	1,000MΩ		500 V DC

Note: Recommendable LED forward current I_F = 5 to 10mA.

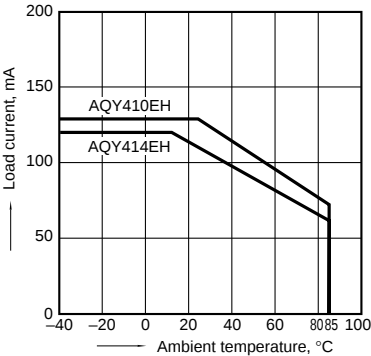
For type of connection



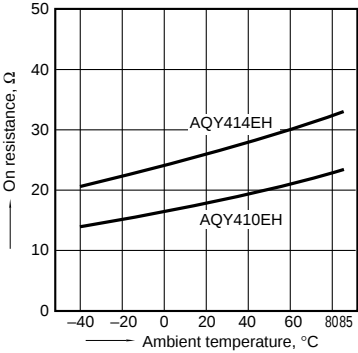
- For Dimensions, see Page 440.
- For Schematic and Wiring Diagrams, see Page 445.
- For Cautions for Use, see Page 449.

REFERENCE DATA

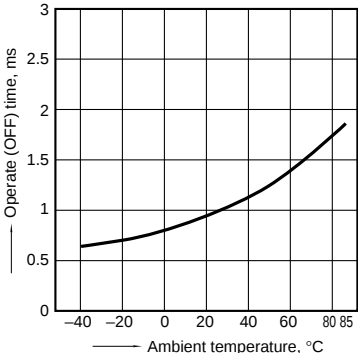
1. Load current vs. ambient temperature characteristics
Allowable ambient temperature: -40°C to +85°C
-40°F to +185°F



2. On resistance vs. ambient temperature characteristics
Measured portion: between terminals 3 and 4;
LED current: 0 mA; Load voltage: Max.(DC);
Continuous load current: Max. (DC)

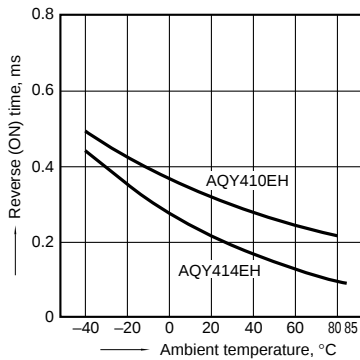


3. Operate (OFF) time vs. ambient temperature characteristics
LED current: 5 mA; Load voltage: Max. (DC);
Continuous load current: Max. (DC)



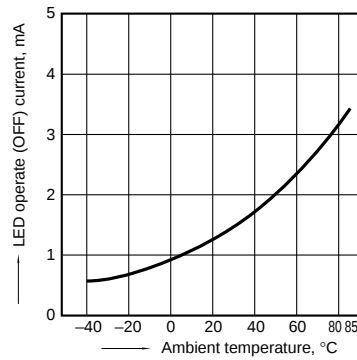
4. Reverse (ON) time vs. ambient temperature characteristics

LED current: 5 mA; Load voltage: Max. (DC);
Continuous load current: Max. (DC)



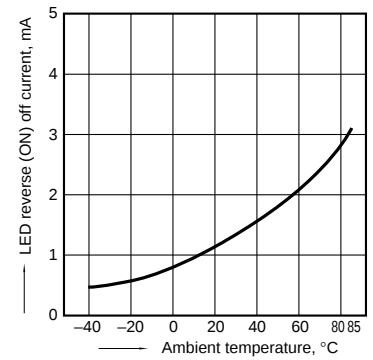
5. LED operate (OFF) current vs. ambient temperature characteristics

Load voltage: Max. (DC);
Continuous load current: Max. (DC)



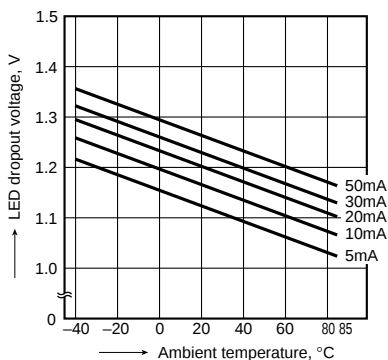
6. LED reverse (ON) current vs. ambient temperature characteristics

Load voltage: Max. (DC);
Continuous load current: Max. (DC)



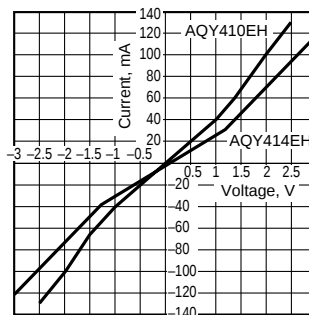
7. LED dropout voltage vs. ambient temperature characteristics

LED current: 5 to 50 mA



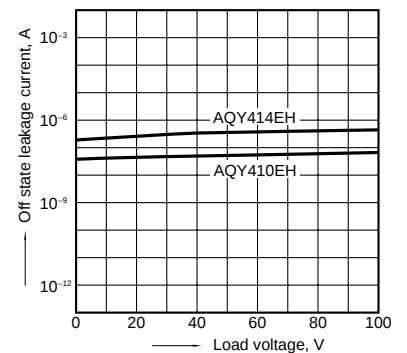
8. Voltage vs. current characteristics of out-put at MOS portion

Measured portion: between terminals 3 and 4;
Ambient temperature: 25°C 77°F



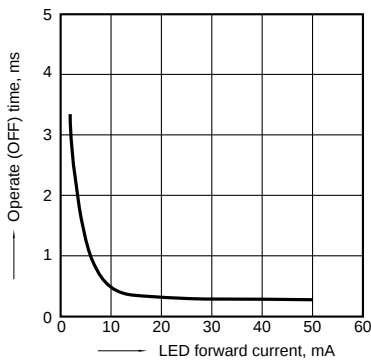
9. Off state leakage current

Measured portion: between terminals 3 and 4;
Ambient temperature: 25°C 77°F



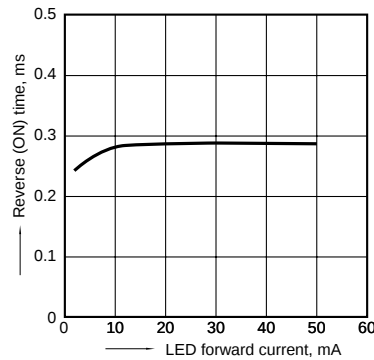
10. LED forward current vs. Operate (OFF) time characteristics

Measured portion: between terminals 3 and 4;
Load voltage: Max. (DC); Continuous load current: Max. (DC); Ambient temperature: 25°C 77°F



11. LED forward current vs. Reverse (ON) time characteristics

Measured portion: between terminals 3 and 4;
Load voltage: Max. (DC); Continuous load current: Max. (DC); Ambient temperature: 25°C 77°F



12. Applied voltage vs. output capacitance characteristics

Measured portion: between terminals 3 and 4;
Frequency: 1 MHz; Ambient temperature: 25°C 77°F

